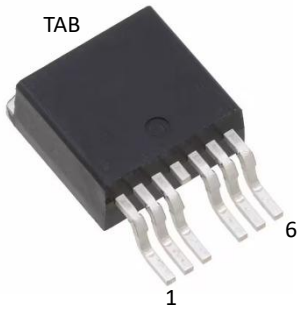
## 1.Description

SS029N10M6S, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

**Schematic Diagram**

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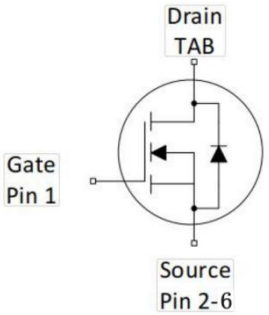


### KEY CHARACTERISTICS

| Parameter | Value | Unit |
|---|---|---|
| $V_{DSS}$ | 100 | V |
| $I_D$ | 210 | A |
| $R_{DS(on).typ}$ | 2.5 | mΩ |

### FEATURES:

- Fast Switching
- Low On-Resistance ( $R_{DS(on)} \leqslant 2.8m\Omega$ )
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

### APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

### ORDERING INFORMATION

| Ordering Codes | Package | Product Code | Packing |
|---|---|---|---|
| SS029N10M6S | TO-263-6L | SS029N10M6S | Reel |